

# CY7C1011CV33

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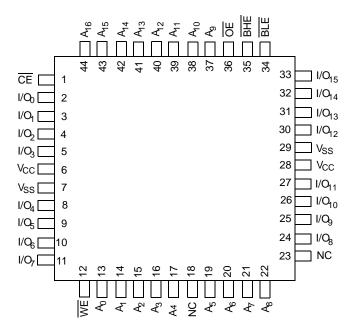




# **Pin Configuration**

Figure 1. 44-pin TSOP II [1]

Figure 2. 44-pin TQFP



Note

1. NC pins are not connected on the die.



# **Selection Guide**

Description	-10	-12	Unit	
Maximum access time		10	12	ns
Maximum operating current	Industrial	100	95	mA
	Automotive-A	100	-	mA
	Automotive-E	_	120	mA
Maximum CMOS standby current	Industrial	10	10	mA
	Automotive-A	10	-	mA
	Automotive-E	_	15	mA



### **Maximum Ratings**

Exceeding maximum ratings may shorten the useful life of the device. These user guidelines are not tested.

Storage temperature65 °C to +150 °C
Ambient temperature with power applied–55 °C to +125 °C
Supply voltage on V <sub>CC</sub> relative to $GND^{[2]}$ –0.5 V to +4.6 V
DC voltage applied to outputs
DC voltage applied to outputs in High Z state $^{[2]}$ 0.5 V to V_{CC}+ 0.5 V
DC input voltage <sup>[2]</sup> 0.5 V to V <sub>CC</sub> + 0.5 V

Current into outputs (LOW)	20 mA
Static discharge voltage (MIL-STD-883, method 3015)	> 2001 V
Latch up current	> 200 mA

# **Operating Range**

Range	Ambient Temperature (T <sub>A</sub> )	V <sub>CC</sub>
Industrial	–40 °C to +85 °C	$3.3~V\pm10\%$
Automotive-A	–40 °C to +85 °C	
Automotive -E	–40 °C to +125 °C	

# **Electrical Characteristics**

Over the Operating Range

Parameter	Description	Test Condition	•		-10		-12	Unit
Farallieler	Description Test Conditions				Max	Min	Max	Unit
V <sub>OH</sub>	Output HIGH voltage	V <sub>CC</sub> = Min, I <sub>OH</sub> = -4.0 mA		2.4	-	2.4	-	V
V <sub>OL</sub>	Output LOW voltage	$V_{CC} = Min, I_{OL} = 8.0 mA$		_	0.4	-	0.4	V
V <sub>IH</sub>	Input HIGH voltage			2.0	V <sub>CC</sub> + 0.3	2.0	V <sub>CC</sub> + 0.3	V
V <sub>IL</sub>	Input LOW voltage <sup>[2]</sup>			-0.3	0.8	-0.3	0.8	V
I <sub>IX</sub>	Input leakage current	$GND \leq V_{I} \leq V_{CC}$	Industrial	-1	+1	-1	+1	μA
			Automotive-A	-1	+1	—	-	
			Automotive-E	-	-	-20	+20	
I <sub>OZ</sub>	Output leakage current	$GND \le V_I \le V_{CC},$ Output disabled	Industrial	-1	+1	-1	+1	μA
			Automotive-A	-1	+1	-	_	
			Automotive-E	-	_	-20	+20	
I <sub>CC</sub>	V <sub>CC</sub> operating supply	$V_{CC} = Max, I_{OUT} = 0 mA,$	Industrial	-	100	—	95	mA
	current	$f = f_{MAX} = 1/t_{RC}$	Automotive-A	-	100	-	_	
			Automotive-E	-	-	—	120	
I <sub>SB1</sub>	Automatic CE power	Max $V_{CC}$ , $\overline{CE} \ge V_{IH}$ ,	Industrial	-	40	—	40	mA
	down current —TTL	$V_{IN} \ge V_{IH}$ or $V_{IN} \le V_{IL}$ , f = f <sub>MAX</sub>	Automotive-A	-	40	-	_	
	Inputs		Automotive-E	-	_	-	45	
I <sub>SB2</sub>	Automatic CE power	Max V <sub>CC</sub> , $\overline{CE} \ge V_{CC} - 0.3$ V,	Industrial	-	10	-	10	mA
	down current — CMOS inputs	$V_{IN} \ge V_{CC} - 0.3 \text{ V}, \text{ or}$ $V_{IN} \le 0.3 \text{ V}, \text{ f} = 0$	Automotive-A	-	10	-	-	
		$V_{\text{IN}} \ge 0.3 V, V = 0$	Automotive-E	-	-	_	15	



## Capacitance

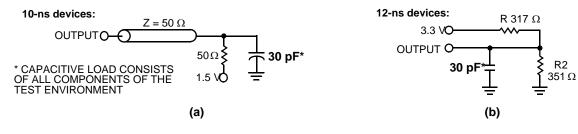
Parameter <sup>[3]</sup>	Description	Max	Unit	
C <sub>IN</sub>	Input capacitance	$T_A = 25 \text{ °C}, f = 1 \text{ MHz}, V_{CC} = 3.3 \text{ V}$	8	pF
C <sub>OUT</sub>	Output capacitance		8	pF

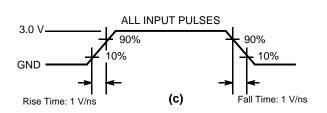
#### **Thermal Resistance**

Parameter <sup>[3]</sup>	Description	Test Conditions	44-pin TSOP II	44-pin TQFP	Unit
$\Theta_{JA}$	Thermal resistance (Junction to ambient)	Still air, soldered on a 3 × 4.5 inch, four-layer printed circuit board	44.56	42.66	°C/W
$\Theta_{JC}$	Thermal resistance (Junction to case)		10.75	14.64	°C/W

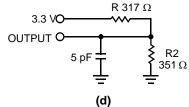
### **AC Test Loads and Waveforms**











Notes

- 3. Tested initially and after any design or process changes that may affect these parameters.
- AC characteristics (except High Z) for 10-ns parts are tested using the load conditions shown in Figure 3 (a). All other speeds are tested using the Thevenin load shown in Figure 3 (b). High Z characteristics are tested for all speeds using the test load shown in Figure 3 (d).



# **Switching Characteristics**

Over the Operating Range

Parameter [5]	<b>D</b>		-	10	-1	2	l Init
	Description	י -	Min	Max	Min	Мах	Unit
Read Cycle	•						
t <sub>power</sub> <sup>[6]</sup>	$V_{CC}$ (typical) to the first access		1	-	1	-	μS
t <sub>RC</sub>	Read cycle time	10	_	12	-	ns	
t <sub>AA</sub>	Address to data valid		_	10	_	12	ns
t <sub>OHA</sub>	Data hold from address change		3	-	3	-	ns
t <sub>ACE</sub>	CE LOW to data valid		_	10	-	12	ns
t <sub>DOE</sub>	OE LOW to data valid	Industrial/Automotive-A	_	5	-	6	ns
		Automotive-E	_	-	-	8	
t <sub>LZOE</sub>	OE LOW to Low Z <sup>[7]</sup>		0	-	0	-	ns
t <sub>HZOE</sub>	OE HIGH to High Z <sup>[7, 8]</sup>		_	5	-	6	ns
t <sub>LZCE</sub>	CE LOW to Low Z <sup>[7]</sup>		3	-	3	-	ns
t <sub>HZCE</sub>	CE HIGH to High Z <sup>[7, 8]</sup>	_	5	_	6	ns	
t <sub>PU</sub>	CE LOW to power up	0	-	0	-	ns	
t <sub>PD</sub>	CE HIGH to power down		_	10	_	12	ns
t <sub>DBE</sub>	Byte enable to data valid	Industrial/Automotive-A	_	5	_	6	ns
		Automotive-E	_	-	_	8	
t <sub>LZBE</sub>	Byte enable to Low Z		0	-	0	-	ns
t <sub>HZBE</sub>	Byte disable to High Z		_	5	_	6	ns
Write Cycle <sup>[§</sup>	9, 10]						•
t <sub>WC</sub>	Write cycle time		10	-	12	_	ns
t <sub>SCE</sub>	CE LOW to write end		7	_	8	-	ns
t <sub>AW</sub>	Address setup to write end		7	_	8	-	ns
t <sub>HA</sub>	Address hold from write end		0	-	0	-	ns
t <sub>SA</sub>	Address setup to write start		0	_	0	-	ns
t <sub>PWE</sub>	WE pulse width	7	-	8	-	ns	
t <sub>SD</sub>	Data setup to write end	5	_	6	-	ns	
t <sub>HD</sub>	Data hold from write end		0	-	0	-	ns
t <sub>LZWE</sub>	WE HIGH to Low Z <sup>[7]</sup>		3	_	3	-	ns
t <sub>HZWE</sub>	WE LOW to High Z <sup>[7, 8]</sup>		_	5	_	6	ns
t <sub>BW</sub>	Byte enable to end of write		7	-	8	-	ns

#### Notes

Notes
5. Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, and input pulse levels of 0 to 3.0 V.
6. t<sub>POWER</sub> gives the minimum amount of time that the power supply is at typical V<sub>CC</sub> values until the first memory access is performed.
7. At any temperature and voltage condition, t<sub>HZCE</sub> is less than t<sub>LZCE</sub>, t<sub>HZOE</sub> is less than t<sub>LZCE</sub>, and t<sub>HZWE</sub> for any device.
8. t<sub>HZOE</sub>, t<sub>HZEE</sub>, t<sub>HZCE</sub>, and t<sub>HZWE</sub> are specified with a load capacitance of 5 pF as in part (d) of Figure 3 on page 6. Transition is measured ±500 mV from steady state voltage
9. The internal write time of the memory is defined by the overlap of CE LOW, WE LOW, and BHE/BLE LOW. CE, WE, and BHE/BLE must be LOW to initiate a write. The transition of these signals terminate the write. The input data setup and hold timing is referenced to the leading edge of the signal that terminates the write.
10. The minimum write cycle time for Write Cycle No. 3 (WE controlled, OE LOW) is the sum of t<sub>HZWE</sub> and t<sub>SD</sub>.



### **Switching Waveforms**

Figure 4. Read Cycle No. 1 (Address Transition Controlled) <sup>[11, 12]</sup>

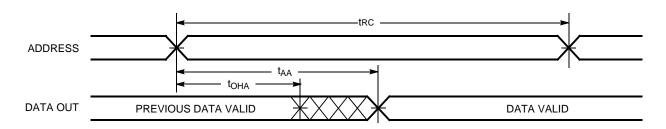
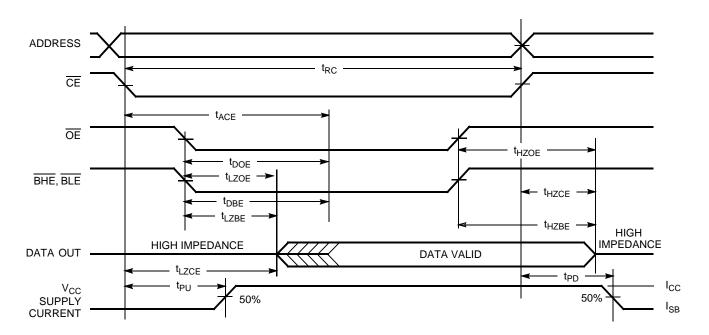


Figure 5. Read Cycle No. 2 (OE Controlled) <sup>[12, 13]</sup>



Notes

11. <u>Device</u> is continuously selected.  $\overline{OE}$ ,  $\overline{CE}$ ,  $\overline{BHE}$ , and/or  $\overline{BLE} = V_{IL}$ . 12. WE is HIGH for read cycle. 13. Address valid prior to or coincident with  $\overline{CE}$  transition LOW.



#### Switching Waveforms (continued)

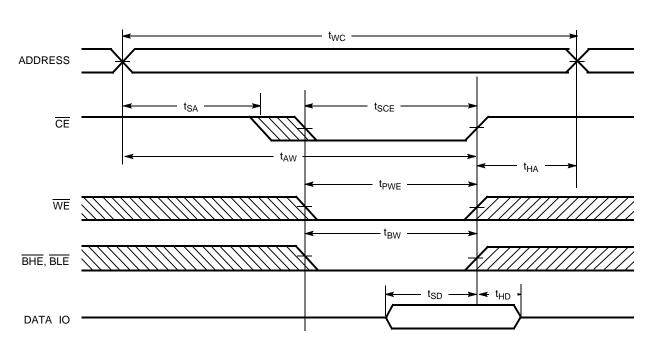
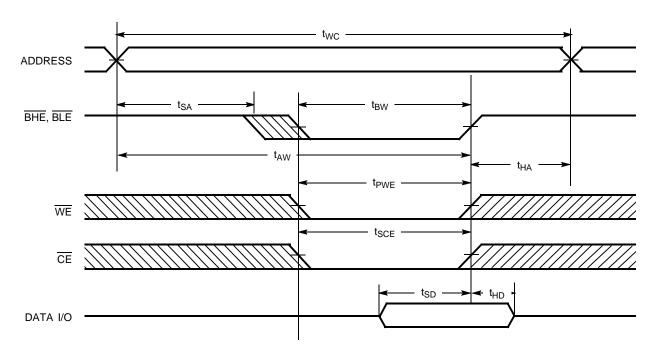


Figure 6. Write Cycle No. 1 (CE Controlled) <sup>[14, 15]</sup>

Figure 7. Write Cycle No. 2 (BLE or BHE Controlled)

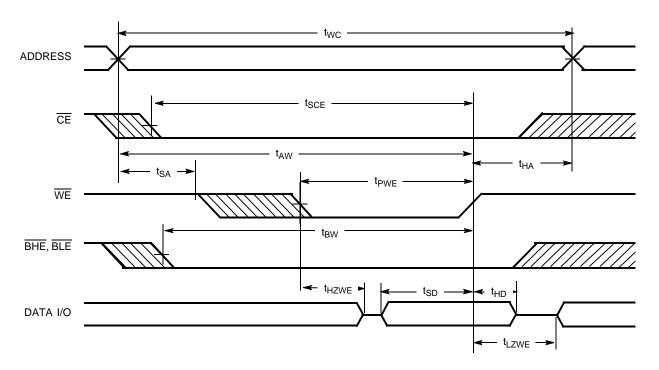


#### Notes

14. Data I/O is high impedance if OE, BHE, and/or BLE = V<sub>IH</sub>.
 15. If CE goes HIGH simultaneously with WE going HIGH, the output remains in a high impedance state.



## Switching Waveforms (continued)



# Figure 8. Write Cycle No. 3 (WE Controlled, LOW)

# Truth Table

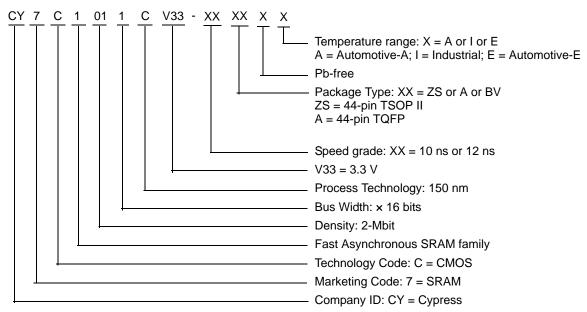
CE	OE	WE	BLE	BHE	1/0 <sub>0</sub> -1/0 <sub>7</sub>	I/O <sub>8</sub> -I/O <sub>15</sub>	Mode	Power
Н	Х	Х	Х	Х	High Z	High Z	Power down	Standby (I <sub>SB</sub> )
L	L	Н	L	L	Data Out	Data Out	Read – all bits	Active (I <sub>CC</sub> )
L	L	Н	L	Н	Data Out	High Z	Read – lower bits only	Active (I <sub>CC</sub> )
L	L	Н	Н	L	High Z	Data Out	Read – upper bits only	Active (I <sub>CC</sub> )
L	Х	L	L	L	Data In	Data In	Write – all bits	Active (I <sub>CC</sub> )
L	Х	L	L	Н	Data In	High Z	Write – lower bits only	Active (I <sub>CC</sub> )
L	Х	L	Н	L	High Z	Data In	Write – upper bits only	Active (I <sub>CC</sub> )
L	Н	Н	Х	Х	High Z	High Z	Selected, outputs disabled	Active (I <sub>CC</sub> )



## **Ordering Information**

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
10	CY7C1011CV33-10ZSXA	51-85087	44-pin TSOP II (Pb-free)	Automotive-A
12	CY7C1011CV33-12AXI	51-85064	44-pin TQFP (Pb-free)	Industrial
	CY7C1011CV33-12ZSXE	51-85087	44-pin TSOP II (Pb-free)	Automotive-E

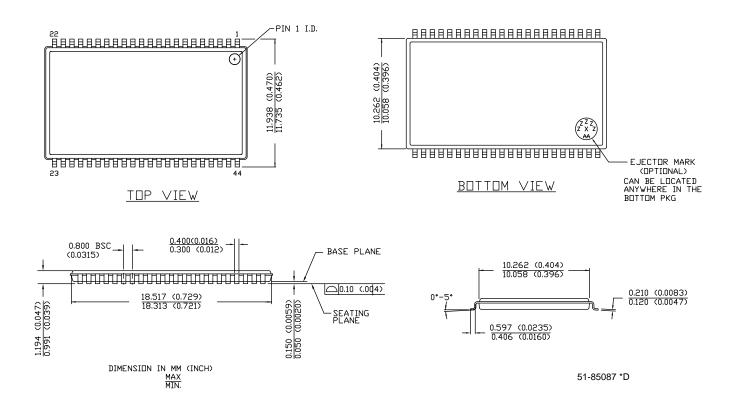
#### **Ordering Code Definitions**





### **Package Diagrams**

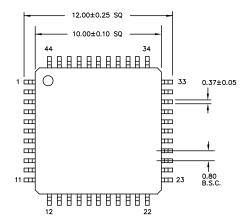
Figure 9. 44-pin TSOP Z44-II, 51-85087

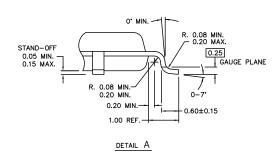




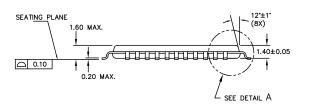
#### Package Diagrams (continued)

Figure 10. 44-pin TQFP (10 × 10 × 1.4 mm) A44S, 51-85064





NOTE:



- NOTE.
- 1. JEDEC STD REF MS-026
- 2. BODY LENGTH DIMENSION DOES NOT INCLUDE MOLD PROTRUSION/END FLASH MOLD PROTRUSION/END FLASH SHALL NOT EXCEED 0.0098 in (0.25 mm) PER SIDE BODY LENGTH DIMENSIONS ARE MAX PLASTIC BODY SIZE INCLUDING MOLD MISMATCH
- 3. DIMENSIONS IN MILLIMETERS

51-85064 \*E





# Acronyms

Acronym	Description			
BHE	byte high enable			
BLE	byte low enable			
CMOS	complementary metal oxide semiconductor			
CE	chip enable			
I/O	input/output			
OE	output enable			
SRAM	static random access memory			
TQFP	thin quad flat pack			
TSOP	thin small outline package			
TTL	transistor-transistor logic			
VFBGA	very fine-pitch ball gird array			
WE	write enable			

### **Document Conventions**

#### **Units of Measure**

Symbol	Unit of Measure			
°C	degree Celsius			
MHz	megahertz			
μA	microampere			
μs	microsecond			
mA	milliampere			
mm	millimeter			
ms	millisecond			
mV	millivolt			
mW	milliwatt			
ns	nanosecond			
%	percent			
pF	pico farad			
V	volt			
W	watt			





# **Document History Page**

#### Document Title: CY7C1011CV33, 2-Mbit (128 K × 16) Static RAM Document Number: 38-05232

Revision	ECN	Orig. of Change	Submission Date	Description of Change
**	117132	HGK	07/31/02	New Data Sheet
*A	118057	HGK	08/19/02	Pin configuration for 48-ball FBGA correction
*B	119702	DFP	10/11/02	Updated FBGA to VFBGA; updated package code on page 8 to BV48A. Updated address pinouts on page 1 to A0 to A16. Updated CMOS standby current on page 1 from 8 to 10 mA
*C	386106	PCI	See ECN	Added lead-free parts in Ordering Information Table
*D	498501	NXR	See ECN	Corrected typo in the Logic Block Diagram on page# 1 Included the Maximum Ratings for Static Discharge Voltage and Latch up Current on page# 3 Changed the description of $I_{IX}$ from Input Load Current to Input Leakage Current in DC Electrical Characteristics table Updated the Ordering Information Table
*E	522620	VKN	See ECN	Added Thermal Resistance Table
*F	1891366	VKN/AESA	See ECN	Added -10ZSXA part Updated Ordering Information table
*G	2428606	VKN/PYRS	See ECN	Corrected typo in the 44-Pin TSOP and 48-Ball FBGA pinout Removed Commercial parts Removed 15 ns speed bin Removed inactive parts from the Ordering Information table
*H	2664421	VKN/AESA	02/25/09	Added Automotive-E specs for 12 ns speed Updated Ordering Information table
*	2898399	KAO/AJU	03/24/2010	Updated Package Diagrams
*J	2950666	VKN	06/11/2010	Included "CY7C1011CV33-12BVXE" in Ordering Information Added Contents and Acronyms Updated Sales, Solutions, and Legal Information Added Ordering Code Definitions.
*K	3089939	PRAS	11/13/2010	Removed inactive part from Ordering Information.
*L	3276463	KAO	06/07/2011	Updated Functional Description (Removed "For best practice recommendations, refer to the Cypress application note AN1064, SRAM System Guidelines."). Added Units of Measure. Updated Package Diagrams. Updated in new template.
*M	3591978	TAVA	04/19/2012	Removed all information related to 48-ball VFBGA throughout the document. Updated package diagram revisions.



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